

**MBD4148W /BAS16W** SWITCHING DIODE**FEATURES**

Power dissipation

P_D: 200 mW (T_{amb}=25°C)

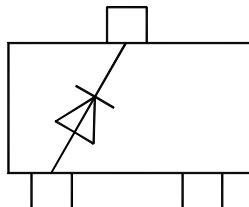
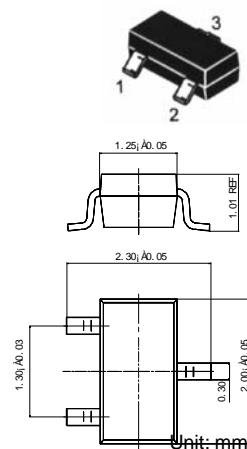
Collector current

I_O: 150 mA

Collector-base voltage

V_R: 75 V

Operating and storage junction temperature range

T_J, T_{stg}: -55°C to +150°C**SOT-323**

Marking: A2, KA2, KT1

ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	V _(BR) R	I _R = 100μA	75		V
Reverse voltage leakage current	I _R	V _R =75V		1	μA
Forward voltage	V _F	I _F =1mA I _F =10mA I _F =50mA I _F =150mA		0.715 0.855 1 1.25	V
Diode capacitance	C _D	V _R =0V, f=1MHz		2	pF
Reveres recovery time	t _{rr}	I _F =I _R =10mA I _{rr} =0.1×I _R		4	nS